



Docket No. 50654

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: T. Adams

SERIAL NO.: 09/825,070

EXAMINER: S. Lee

FILED: April 3, 2001

GROUP: 1752

FOR: PHOTORESIST COMPOSITION AND USE OF SAME

THE HONORABLE COMMISSIONER OF PATENTS AND TRADEMARKS
WASHINGTON, DC 20231

SIR:

AMENDMENT

Applicants are in receipt of the Office Action dated November 15, 2002. Please amend the above-identified application as follows.

IN THE SPECIFICATION

Please amend the third full paragraph of page 6 (currently lines 11-16) to read as follows:

As discussed above, the resists should not significantly crosslink during pre-exposure softbake temperatures (e.g. about 110°C or less, for no more than about 1 minute) or during any post-exposure, pre-development thermal treatment that may be employed to promote the latent image patterned into exposed resist areas. Such post-exposure, pre-development thermal treatment is frequently conducted at about 110°C, 120°C or 125°C for no more than 1 minute. Suitably a photoresist is heated after exposure and prior to development at a temperature of not greater than about 120°C, and pre-development heating does not cause substantial crosslinking of the photoresist layer.

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